

## ABSTRACT

Material gas hits the outer peripheral surface of a dam member and rides on the upper surface side, and then is allowed to flow along the main surface of a silicon single-crystal substrate placed on a susceptor. An upper lining member is disposed above the dam member so as to face the dam member. A gas introducing clearance is formed between the dam member and the upper lining member. In a vapor growth device, the upper lining member is regulated in size so that the length, formed in a direction along the horizontal reference line, of the gas introducing clearance gradually decreases as it is away from the horizontal reference line or is kept constant at any position. A vapor growth device capable of making more uniform the flowing route of a material gas flowing on the silicon single-crystal substrate, and a production method for an epitaxial wafer are provided.